Silicon NPN Power Transistors 2SD1264 2SD1264A

DESCRIPTION

·With TO-220Fa package
·Complement to type 2SB940/940A
·High collector to emitter voltage V_{CEO}
·Large collector power dissipation P_C

APPLICATIONS

·For power amplification
·For TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

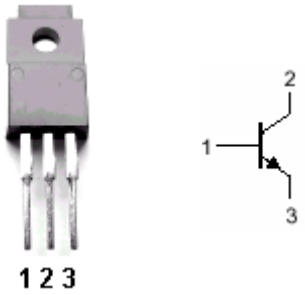

Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	200	V
V_{CEO}	Collector-emitter voltage	2SD1264	Open base	150	V
		2SD1264A		180	
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current			2	A
I_{CM}	Collector current-peak			3	A
P_C	Collector power dissipation		T_a=25□	2	W
			T_C=25□	30	
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter voltage	2SD1264	I_C=5mA ,I_B=0	150			V
		2SD1264A		180			
V_{CBO}	Collector-base voltage		I_C=50μA ,I_E=0	200			V
V_{EBO}	Emitter-base voltage		I_C=500μA ,I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=0.5A, I_B=50mA			1.0	V
V_{BE}	Base-emitter voltage		I_C=0.4A ; V_{CE}=10V			1.0	V
I_{EBO}	Emitter cut-off current		V_{EB}=4V; I_C=0			50	μA
I_{CBO}	Collector cut-off current		V_{CB}=200V; I_E=0			50	μA
h_{FE-1}	DC current gain		I_C=0.15A ; V_{CE}=10V	60		240	
h_{FE-2}	DC current gain		I_C=0.4A ; V_{CE}=10V	50			
f_T	Transition frequency		I_C=0.5A; V_{CE}=10V,f=10MHz		20		MHz

◆ **h_{FE-1} Classifications**

Q	P
60-140	100-240

PACKAGE OUTLINE

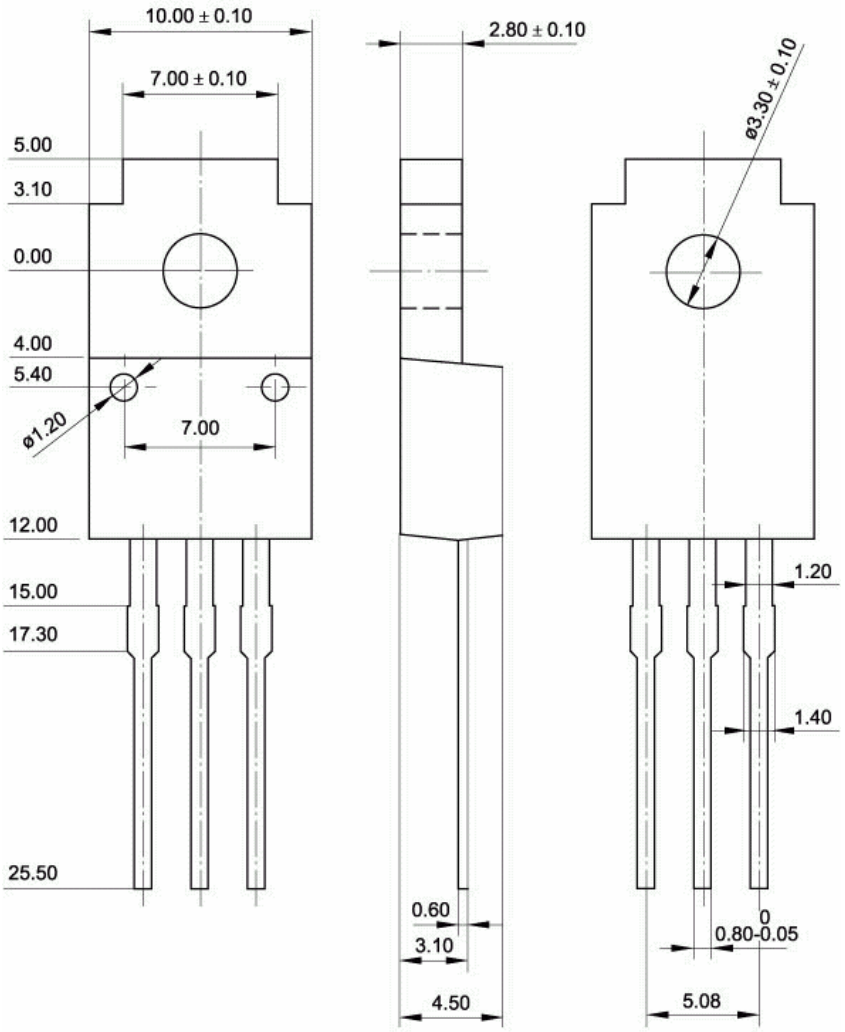

Fig.2 Outline dimensions (unindicated tolerance: ±0.15 mm)

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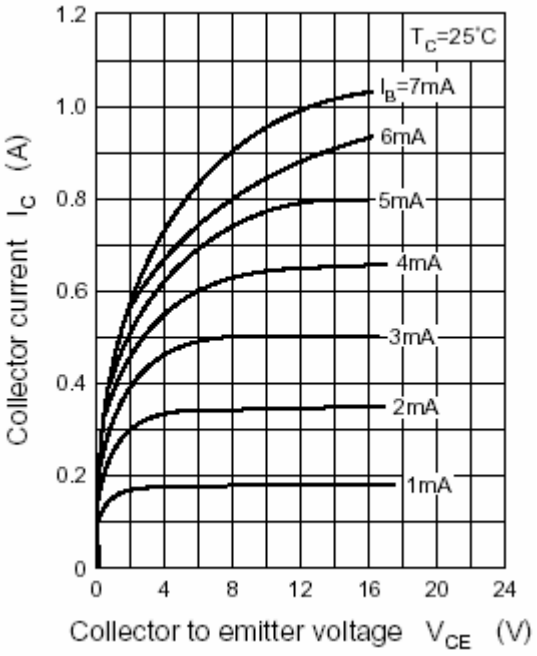

Fig.3 Static Characteristic

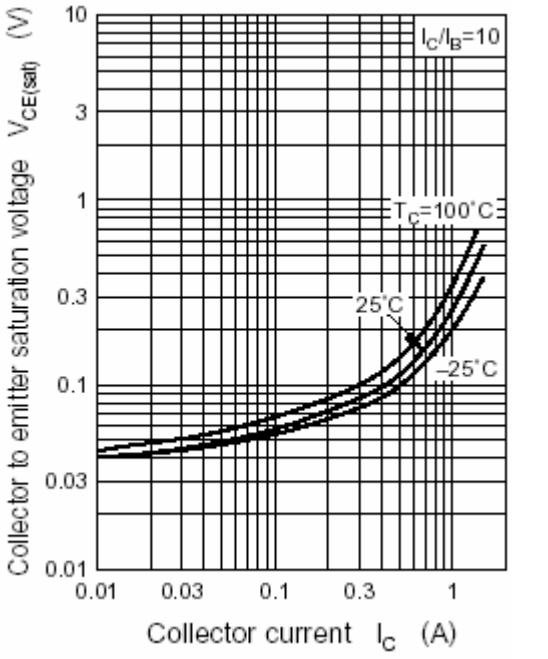

Fig.4 Collector-Emitter Saturation Voltage

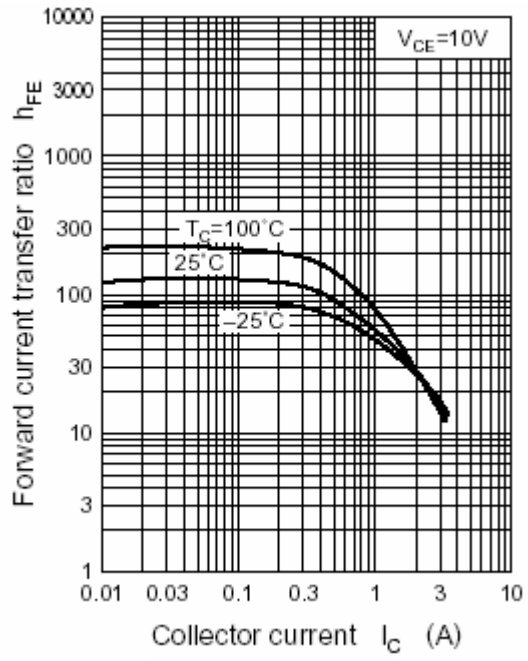

Fig.5 DC current Gain

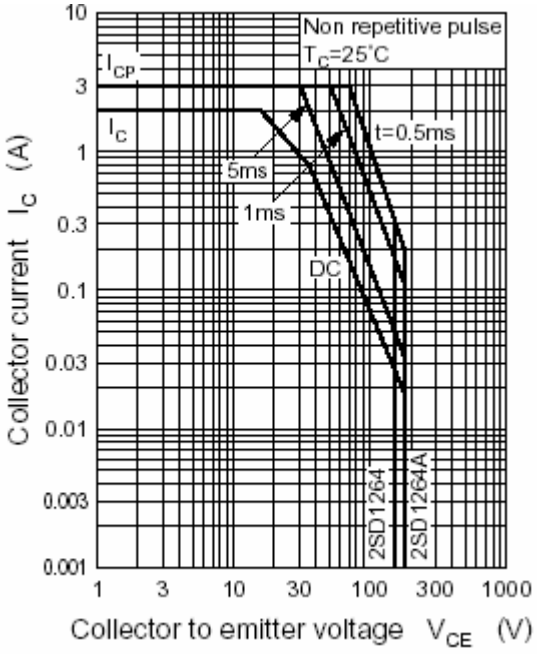

Fig.6 Safe Operating Area